

## **IN THE SPECIFICATION**

Please amend the sentence beginning on page 1, line 5, to read as follows:

This application is a continuation of application serial no. 09/740,256, filed December 19, 2000, which is a continuation of application serial no. 09/344,604, filed June 25, 1999[[9]], which is a divisional of application serial no. 08/854,220, filed on May 9, 1997.

Please also amend the sentence beginning on page 3, line 15, to read as follows:

While non-volatile memories that permit limited reprogramming exist, such as electrically erasable and programmable “ROMs,” all true random access memories, i.e., those memories capable of  $10^{14}$  programming cycles ~~are or~~ more, are volatile memories.

Further, please amend the passage consisting of two sentences beginning on page 8, line 3, and ending on page 8, line 4 to read:

The layer of dielectric material has a ~~port~~pore therein. The pore is smaller ~~that~~than the photolithographic limit.

Please amend the sentence beginning on page 15, line 6, to read:

It is not ~~unusual-unusual~~ for a chalcogenide resistor to demonstrate a wide dynamic range of attainable resistance values of about two orders of magnitude.